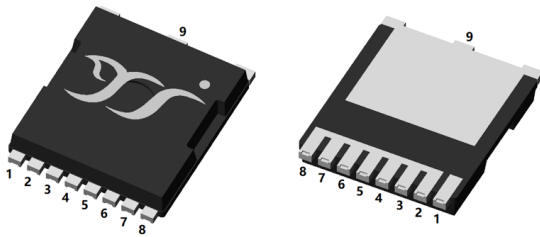


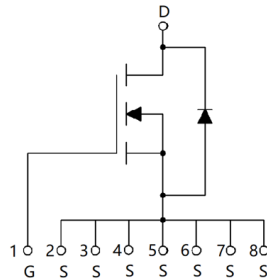
N-Channel Enhancement Mode Field Effect Transistor



Top View

Bottom View

TOLL



Product Summary

- V_{DS} 100 V
- I_D 300 A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) $< 1.45m\Omega$
- $R_{DS(ON)}$ (at $V_{GS}=6V$) $< 1.9m\Omega$
- 100% EAS Tested
- 100% ∇V_{DS} Tested

General Description

- Surface-mounted package
- Excellent package for heat dissipation
- High Density Cell Design for Low $R_{DS(on)}$
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating

Applications

- High power inverter system
- Uninterruptible power supply
- LCDM appliances

■ Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	100	V
Gate-source Voltage		V_{GS}	± 20	V
Drain Current	$T_A=25^\circ C$	I_D	30	A
	$T_A=100^\circ C$		19	
	$T_C=25^\circ C$		300	
	$T_C=100^\circ C$		190	
Pulsed Drain Current ^A		I_{DM}	1200	A
Avalanche energy ^B		EAS	480	mJ
Total Power Dissipation ^C	$T_A=25^\circ C$	P_D	4.15	W
	$T_A=100^\circ C$		1.65	
	$T_C=25^\circ C$		500	
	$T_C=100^\circ C$		200	
Junction and Storage Temperature Range		T_J, T_{STG}	-55~+150	$^\circ C$

■ Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient ^D	Steady-State	$R_{\theta JA}$	20	30	$^\circ C/W$
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	0.2	0.25	

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJT300G10HJ	F1	YJT300G10HJ	2000	4000	20000	13" reel



YJT300G10HJ

■ Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	100	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V	-	-	1	μA
		V _{DS} =100V, V _{GS} =0V, T _J =150°C	-	-	100	
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2	2.9	4	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =30A	-	1.2	1.45	mΩ
		V _{GS} =6V, I _D =15A	-	1.48	1.9	
Diode Forward Voltage	V _{SD}	I _S =30A, V _{GS} =0V	-	0.9	1.3	V
Maximum Body-Diode Continuous Current	I _S		-	-	300	A
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V, f=1MHz	-	13000	-	pF
Output Capacitance	C _{oss}		-	2100	-	
Reverse Transfer Capacitance	C _{rss}		-	120	-	
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =10V, V _{DS} =50V, I _D =30A	-	240	-	nC
Gate-Source Charge	Q _{gs}		-	60	-	
Gate-Drain Charge	Q _{gd}		-	60	-	
Reverse Recovery Charge	Q _{rr}	I _F =30A, di/dt=100A/us	-	380	-	nC
Reverse Recovery Time	t _{rr}		-	130	-	ns
Turn-on Delay Time	t _{D(on)}	V _{GS} =10V, V _{DD} =50V, I _D =30A R _{GEN} =2.2Ω	-	30	-	ns
Turn-on Rise Time	t _r		-	60	-	
Turn-off Delay Time	t _{D(off)}		-	160	-	
Turn-off fall Time	t _f		-	70	-	

A. Repetitive rating; pulse width limited by max. junction temperature.

B. T_J=25°C, V_{DD}=50V, V_G=10V, R_G=25Ω, L=1mH, I_{AS}=31A.

C. P_d is based on max. junction temperature, using junction-case thermal resistance.

D. The value of R_{θJA} is measured with the device mounted on the minimum recommend pad size, in the still air environment with T_A=25°C. The maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.



YJT300G10HJ

Typical Electrical and Thermal Characteristics Diagrams

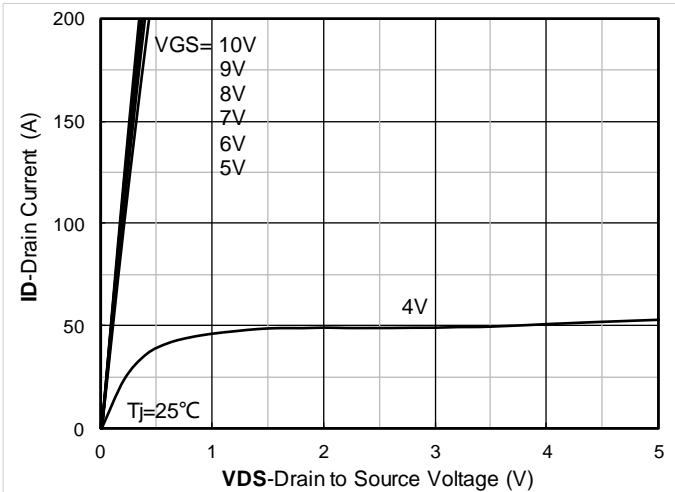


Figure 1. Output Characteristics

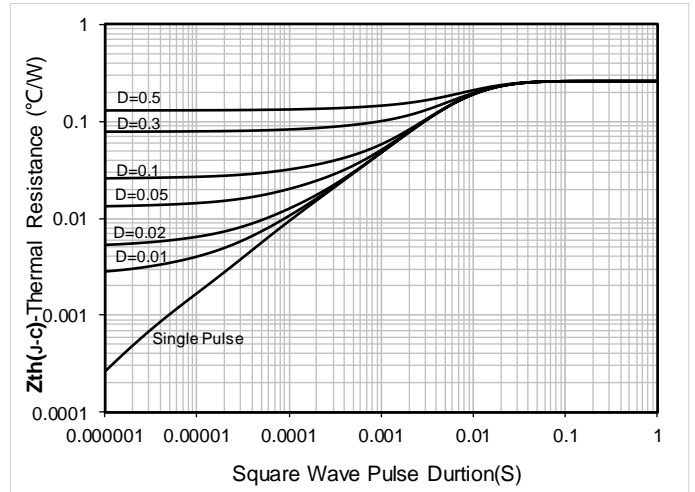


Figure 2. Maximum Transient Thermal Impedance

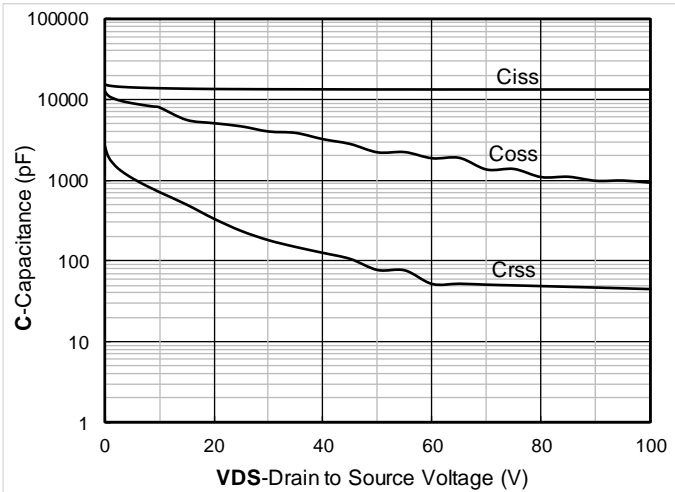


Figure 3. Capacitance Characteristics

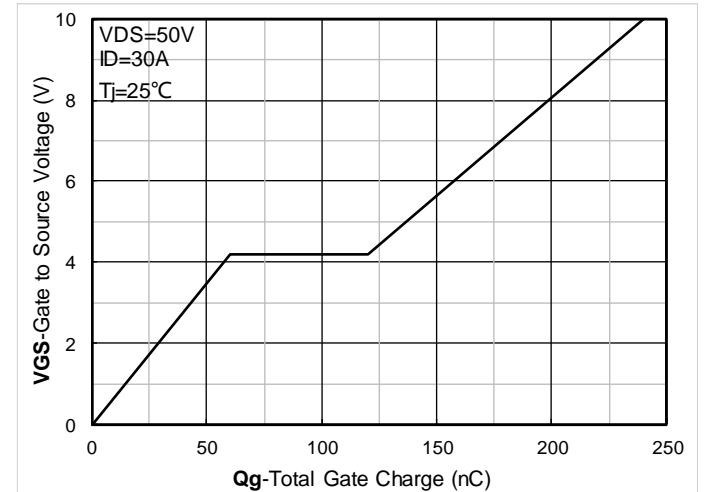


Figure 4. Gate Charge

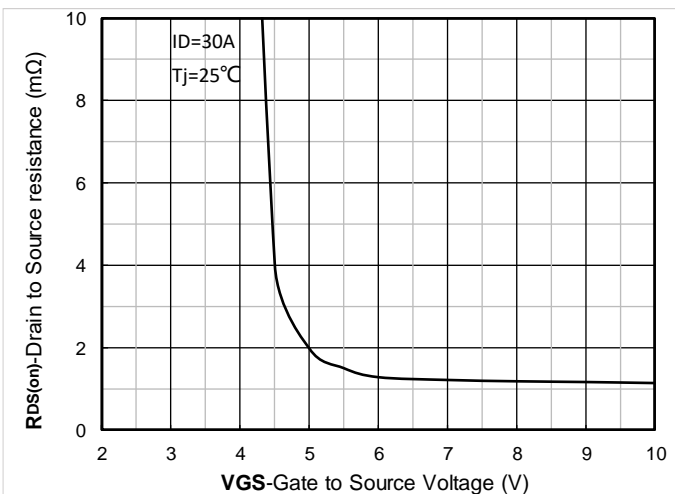


Figure 5. On-Resistance vs Gate to Source Voltage

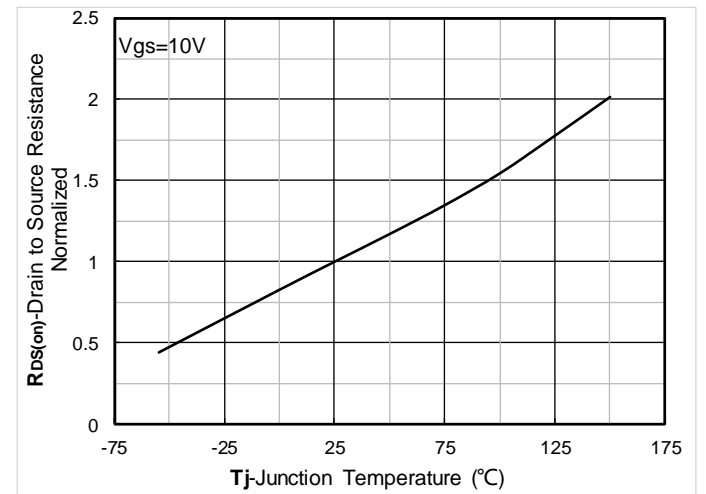


Figure 6. Normalized On-Resistance



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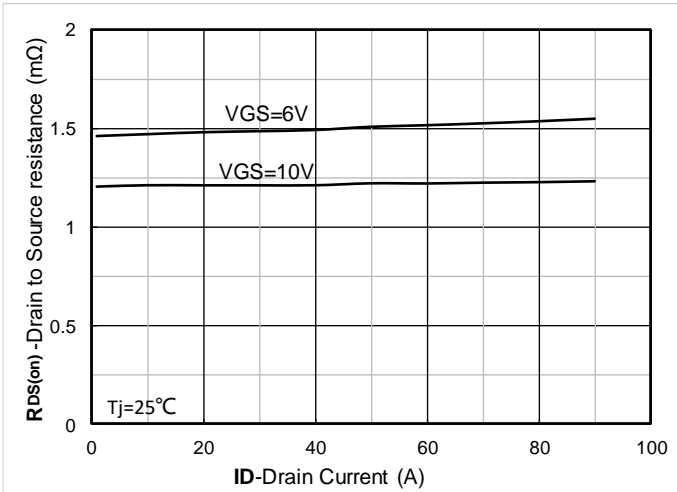


Figure 7. $R_{DS(on)}$ VS Drain Current

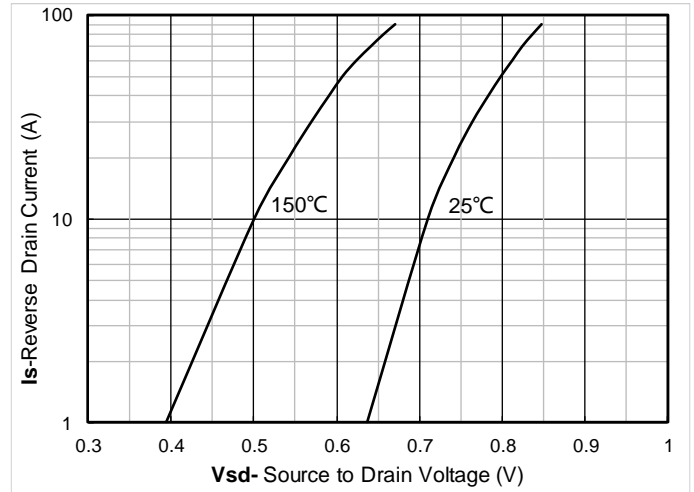


Figure 8. Forward characteristics of reverse diode

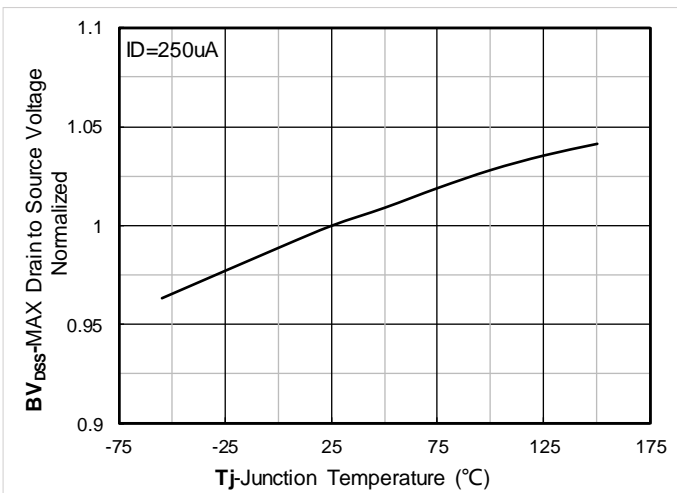


Figure 9. Normalized breakdown voltage

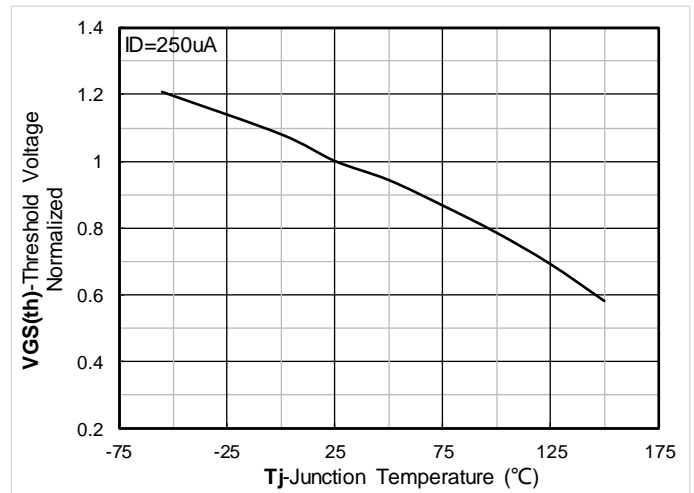


Figure 10. Normalized Threshold voltage

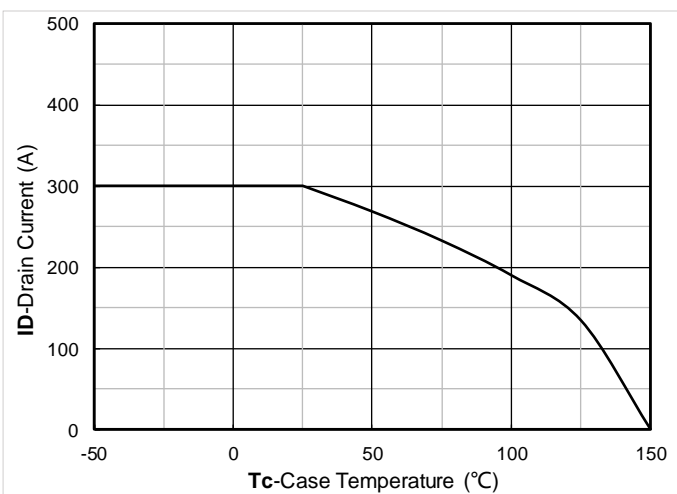


Figure 11. Current dissipation

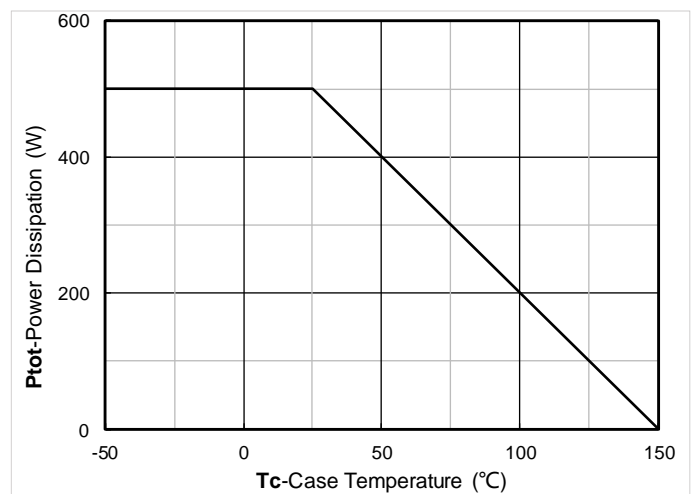


Figure 12. Power dissipation

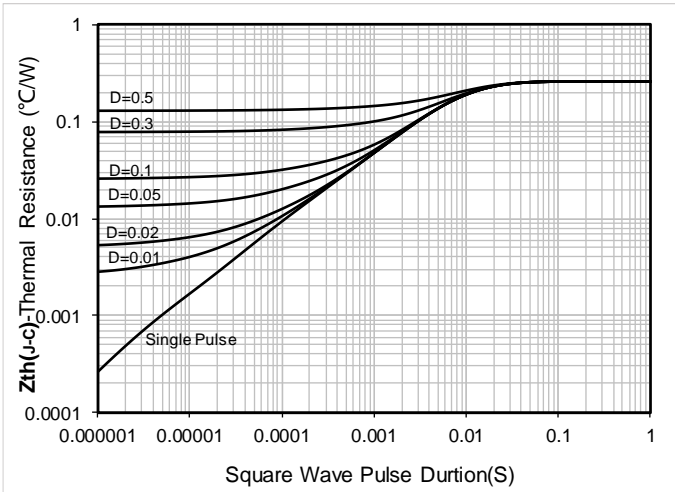


Figure 13. Maximum Transient Thermal Impedance

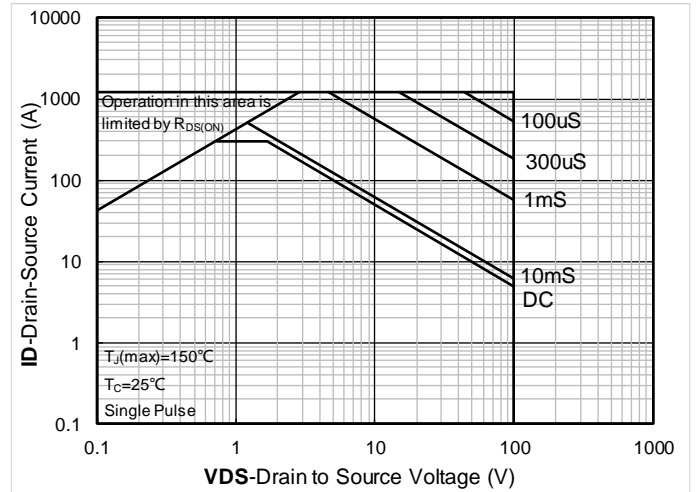


Figure 14. Safe Operation Area

■ Test Circuits & Waveforms

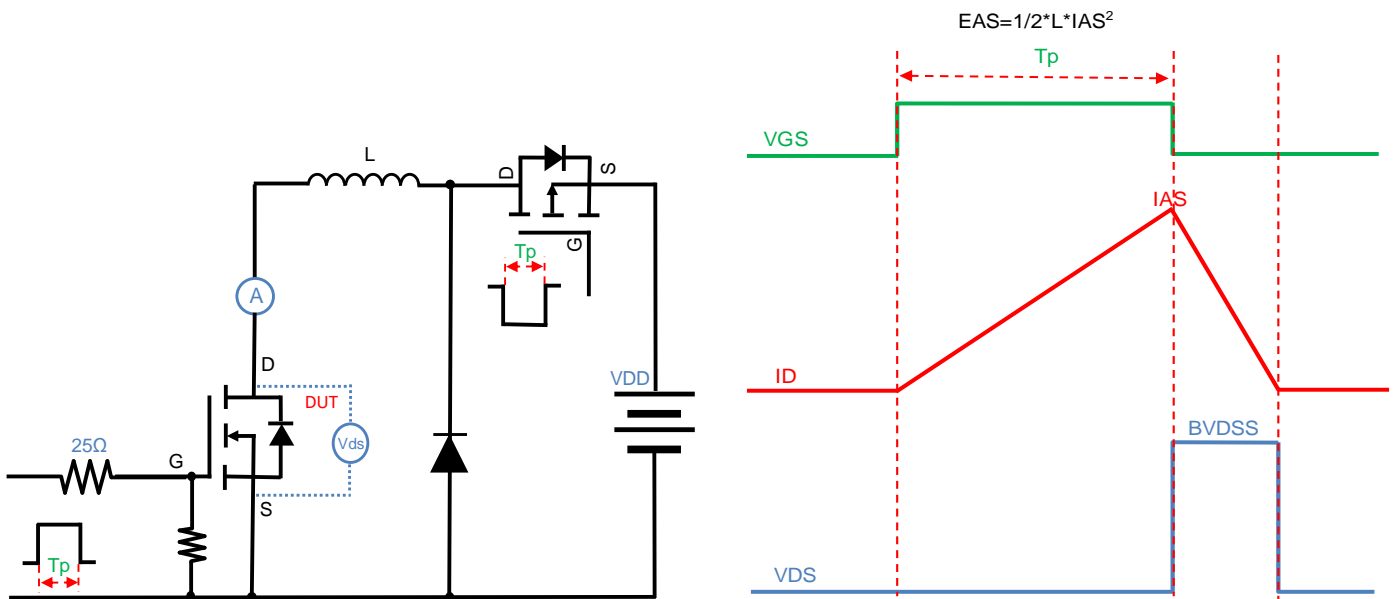
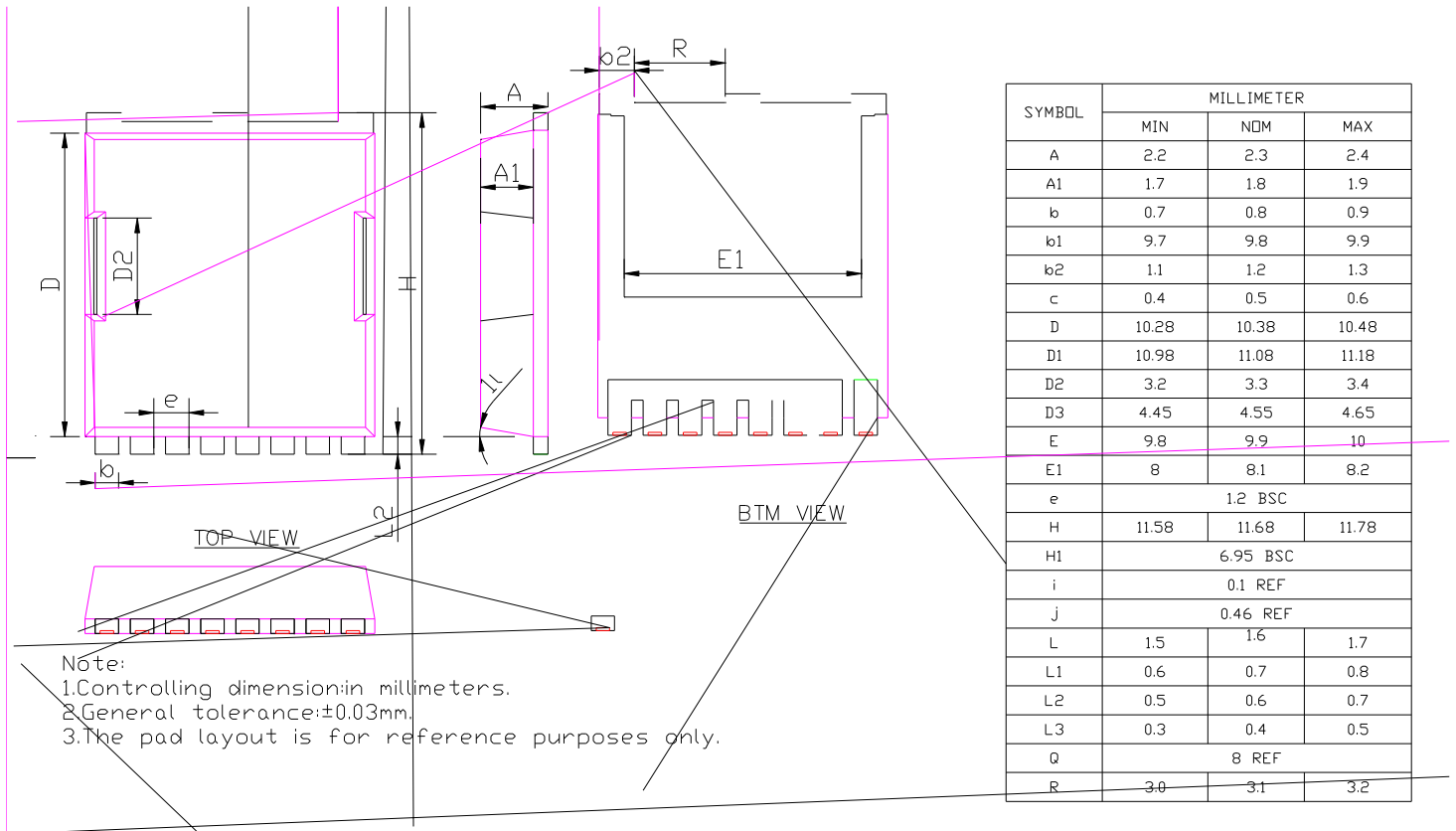


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform



YJT300G10HJ

■ TOLL Package information





YJT300G10HJ

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